

## Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	85mΩ @ V <sub>GS</sub> = 10V	2.5A
	120mΩ @ V <sub>GS</sub> = 4.5V	2.0A

## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Backlighting

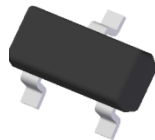
## Features and Benefits

- N MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
- <https://www.diodes.com/quality/product-definitions/>
- An automotive-compliant part is available under a separate datasheet ([DMN6075SQ](#))

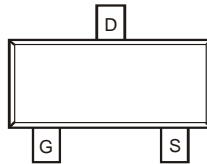
## Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.008 grams (Approximate)

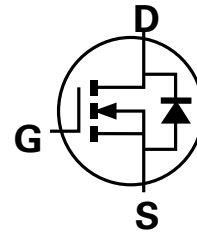
SOT23



Top View



Top View



Top View  
Pin Configuration

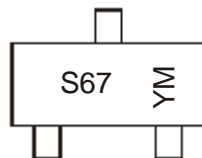
## Ordering Information (Note 4)

Orderable Part Number	Package	Reel Size (inches)	Tape Width (mm)	Packing	
				Qty.	Carrier
DMN6075S-7	SOT23	7	8	3,000	Tape & Reel
DMN6075S-13	SOT23	13	8	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

SOT23



S67 = Product Type Marking Code  
YM = Date Code Marking  
Y or Ȳ = Year (ex: M = 2025)  
M = Month (ex: 9 = September)

### Date Code Key

Year	2014	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	B	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	2.0	A
		T <sub>A</sub> = +70°C		1.5	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	2.5	A
		T <sub>A</sub> = +70°C		2.0	
Maximum Body Diode Forward Current (Note 5)			I <sub>S</sub>	2.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	12	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.8	W
	T <sub>A</sub> = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	157	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.15	W
	T <sub>A</sub> = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	110	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	—	2.7	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	69	85	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.2A
			75	120		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.8A
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.2	V	V <sub>GS</sub> = 0, I <sub>S</sub> = 2.5A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	606	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	32.6	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	24.6	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.5	—	Ω	V <sub>DS</sub> = 0, V <sub>GS</sub> = 0, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	12.3	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 3A
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.6	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	1.7	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.5	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, R <sub>g</sub> = 20Ω, R <sub>L</sub> = 50Ω
Turn-On Rise Time	t <sub>r</sub>	—	4.1	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	35	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	11	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.  
7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

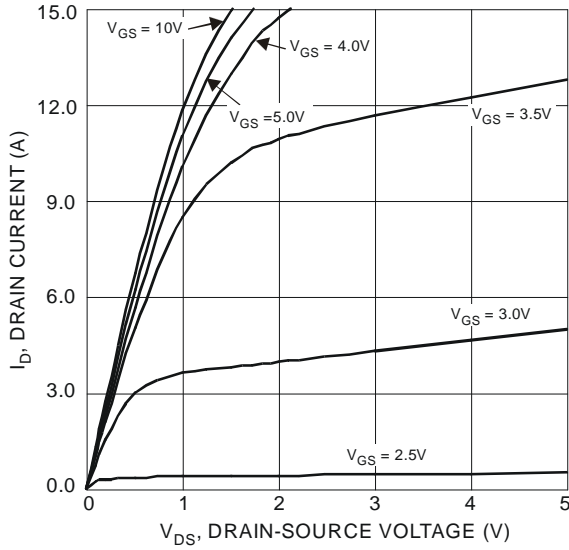


Figure 1 Typical Output Characteristics

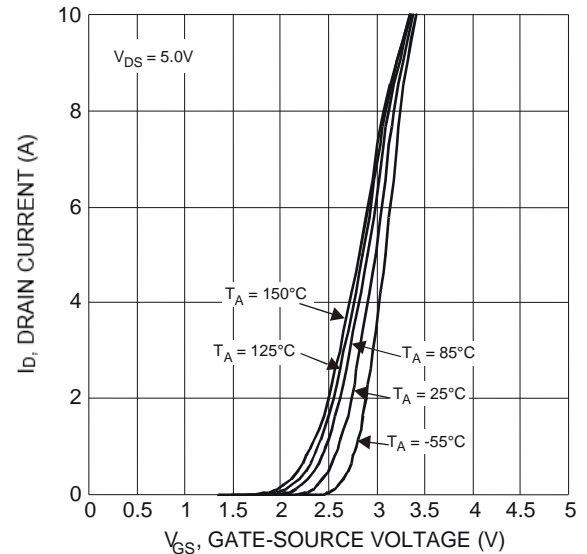


Figure 2 Typical Transfer Characteristics

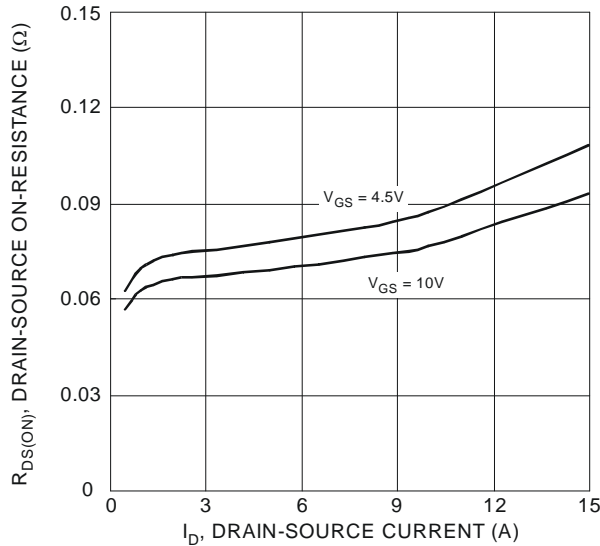


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

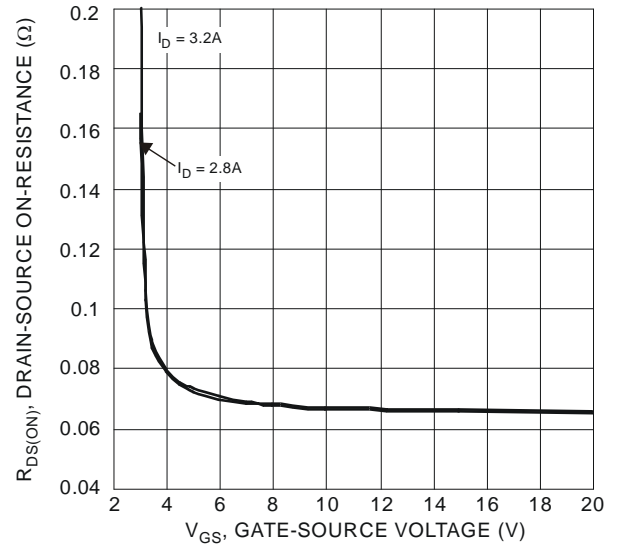


Figure 4 Typical Transfer Characteristics

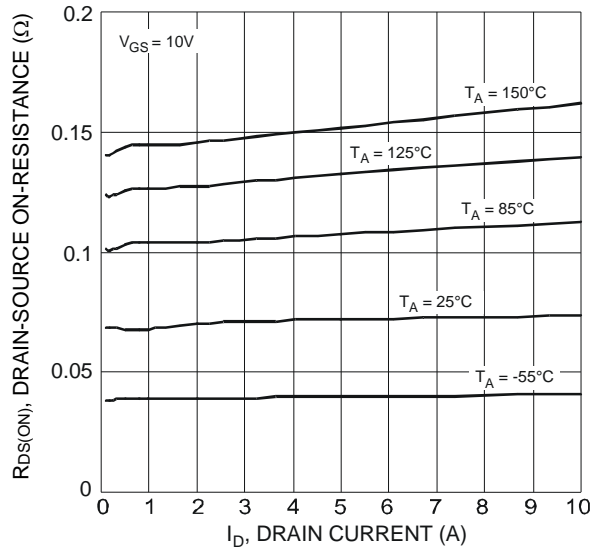


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

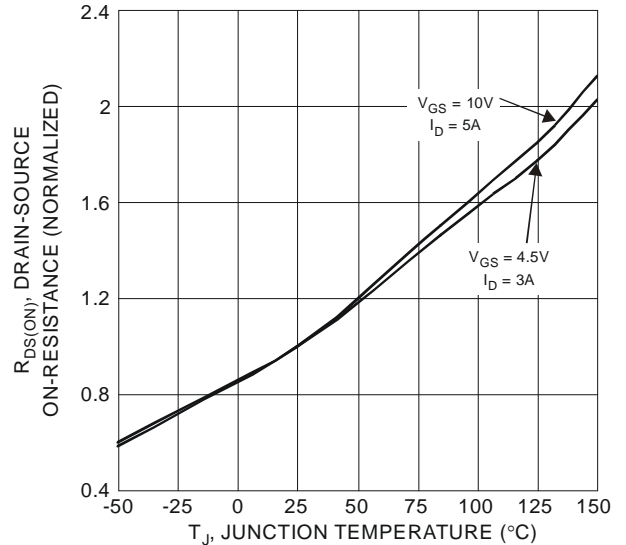
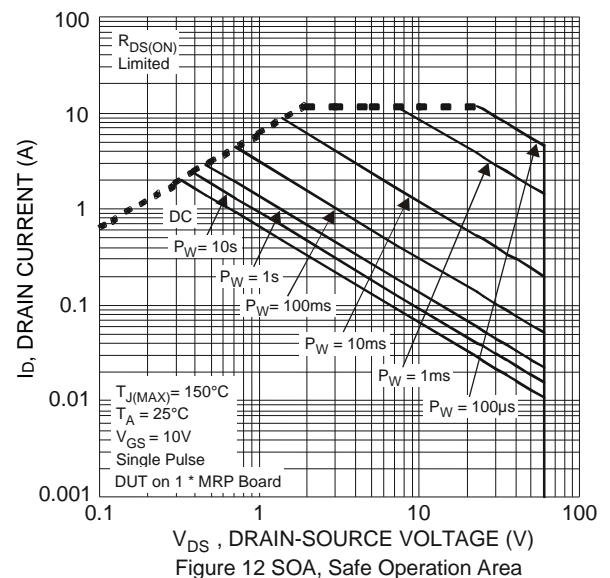
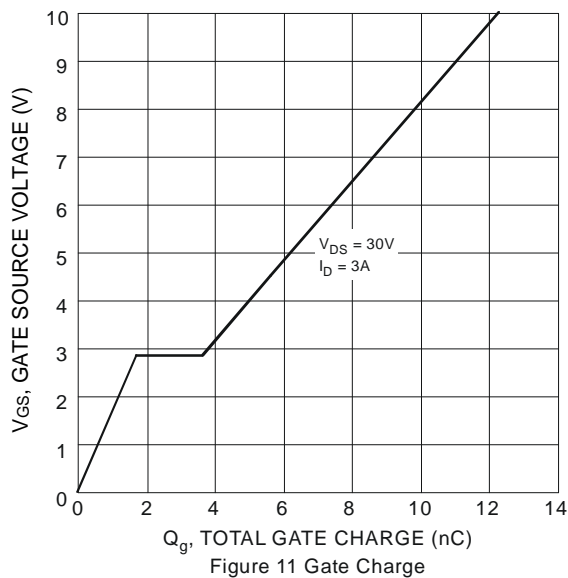
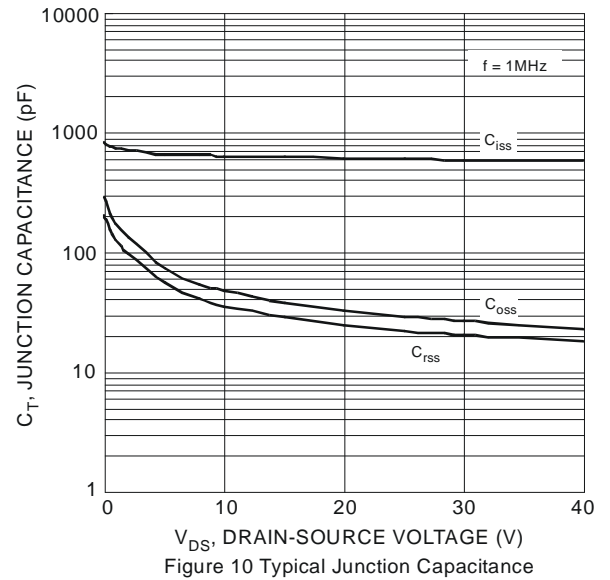
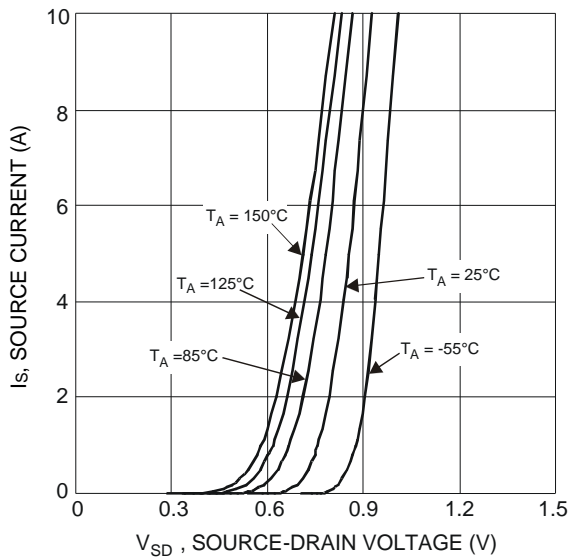
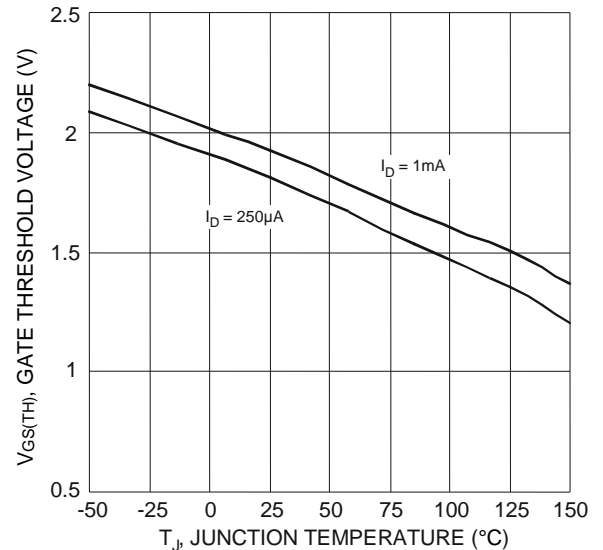
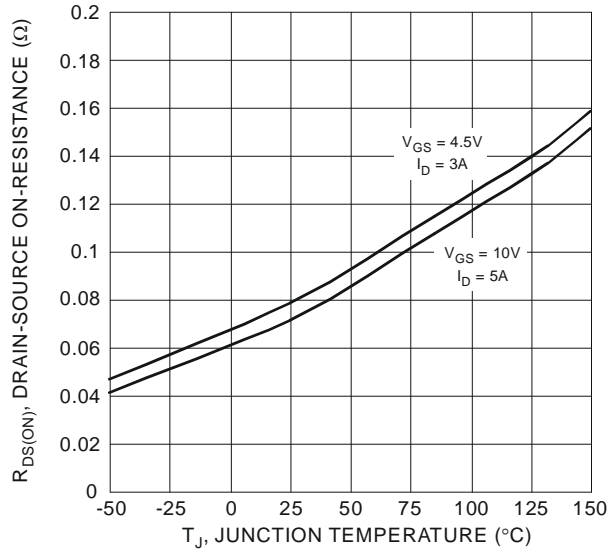


Figure 6 On-Resistance Variation with Temperature



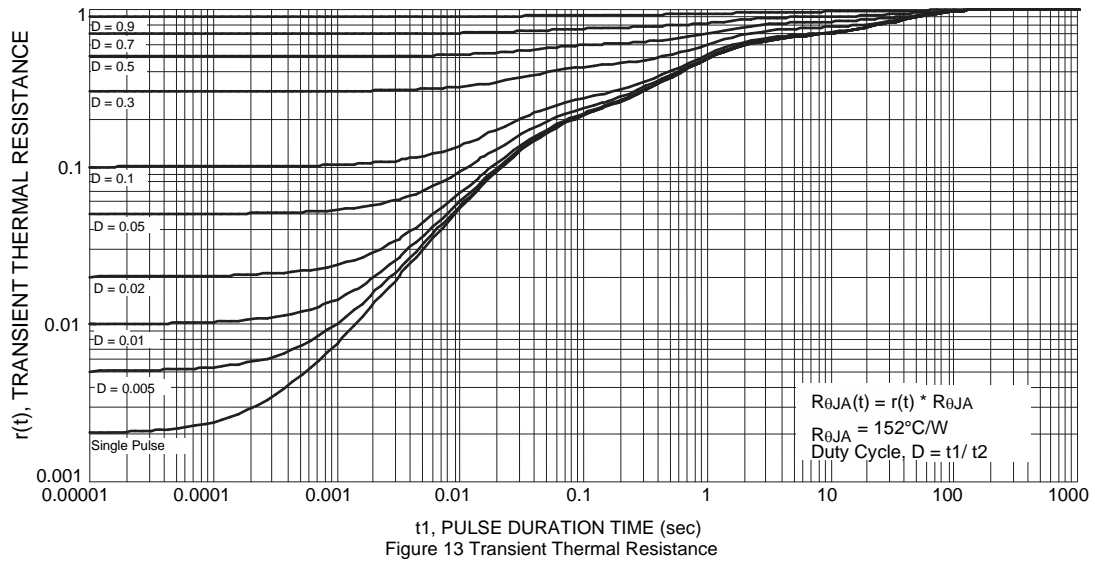
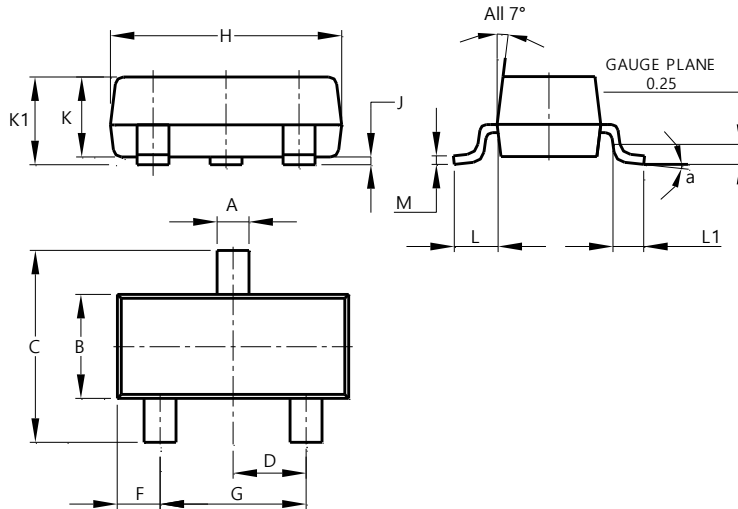


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23

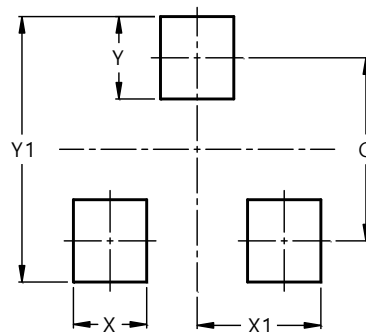


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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